



General Description

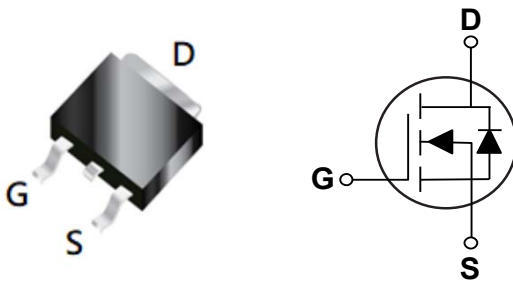
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	$R_{DS(ON)}$	I_D
40 V	6.6 m Ω	75 A

Features

- $R_{DS(ON)} \leq 6.6m\Omega @ V_{GS}=10V$
- Improved dv/dt Capability
- Fast Switching
- Green Device Available

TO-252 Pin Configuration



Applications

- Power Management Switches
- DC/DC Converter

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current - Continuous ($T_C=25^\circ\text{C}$)	75	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	161	A
E_{AS}	Single Pulse Avalanche Energy (NOTE 2)	88	mJ
I_{AS}	Single Pulse Avalanche Current (NOTE 2)	42	A
P_D	Power Dissipation ($T_C=25^\circ\text{C}$)	44.6	W
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
Marking Code		ND6P6	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	75	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	2.8	$^\circ\text{C/W}$



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =40V, V _{GS} =0V	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A	---	---	6.6	mΩ
		V _{GS} =4.5V, I _D =10A	---	---	8.8	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	---	28	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q _g	Total Gate Charge	V _{DD} =20V, V _{GS} =4.5V, I _D =10A	---	20.5	---	nC
Q _{gs}	Gate-Source Charge		---	5.9	---	
Q _{gd}	Gate-Drain Charge		---	9.7	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω, I _D =1A	---	15.4	---	nS
T _r	Rise Time		---	9	---	
T _{d(off)}	Turn-Off Delay Time		---	76	---	
T _f	Fall Time		---	7.1	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3310	---	pF
C _{oss}	Output Capacitance		---	280	---	
C _{rss}	Reverse Transfer Capacitance		---	209	---	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	75	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A	---	---	1	V

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=42A.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



Characteristics Curves

FIG. 1-Output Characteristics

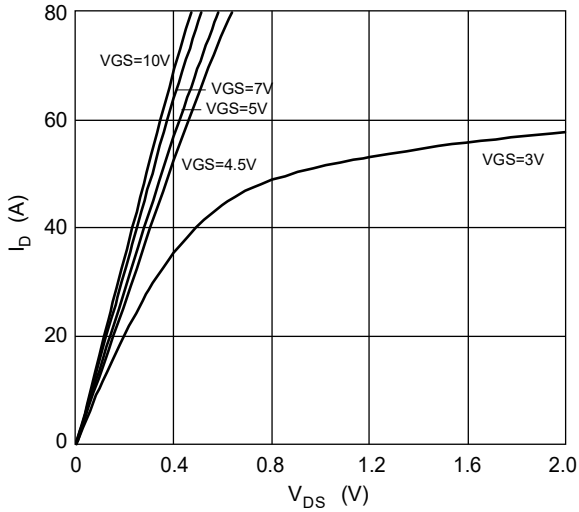


FIG. 2-Transfer Characteristics

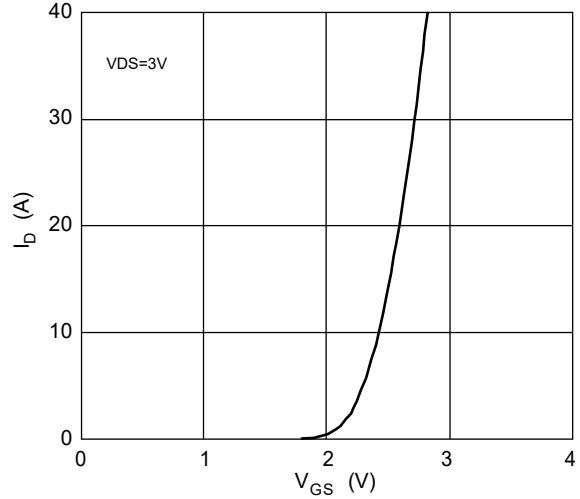


FIG. 3-Normalized $R_{DS(ON)}$ vs. I_D

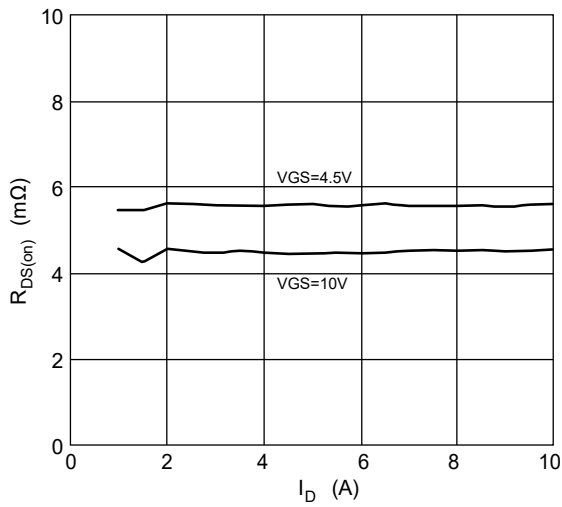


FIG. 4-Gate Charge Characteristics

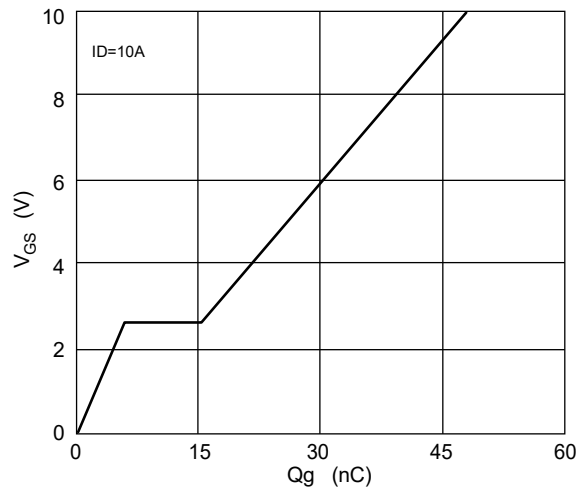


FIG. 5-Safe Operating Area

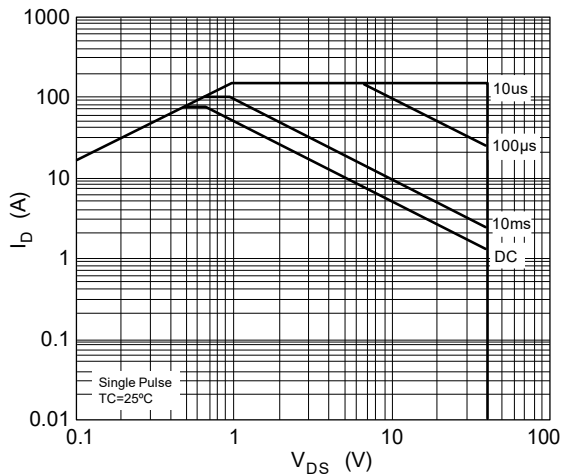
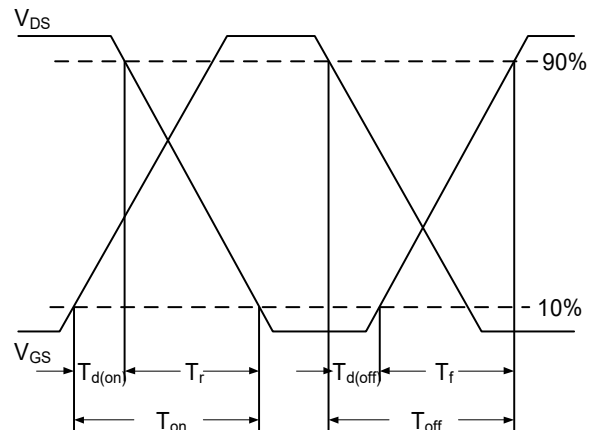
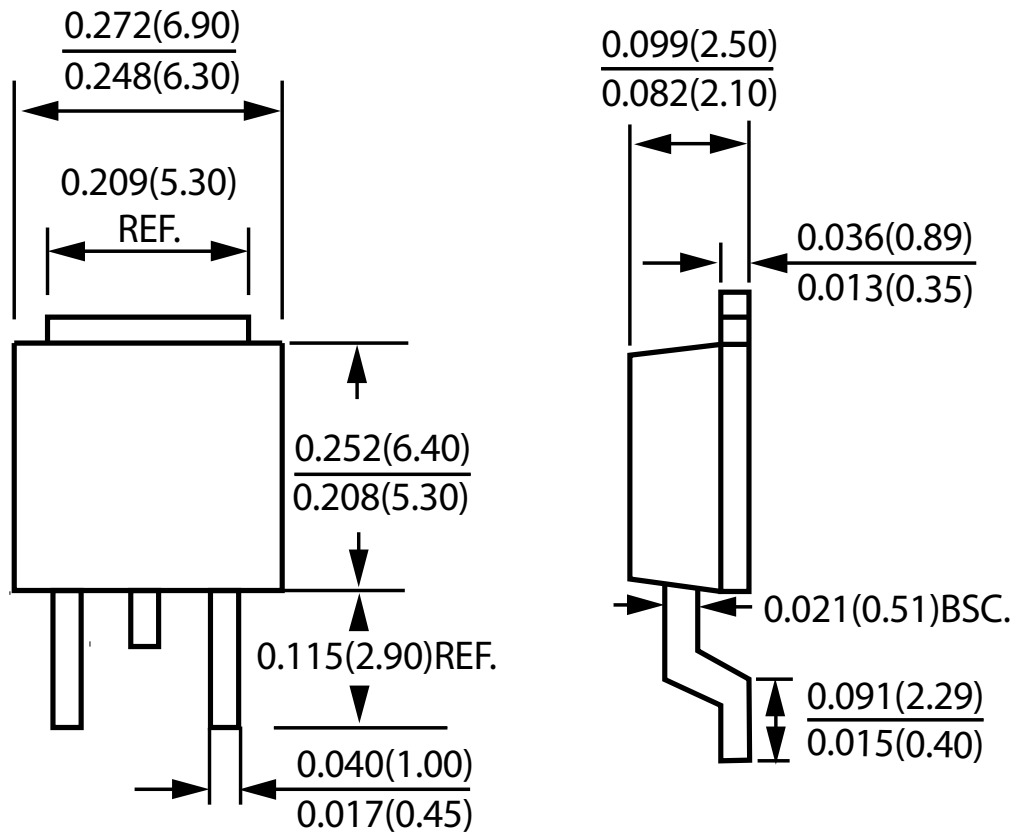


FIG. 6-Switching Time Waveform





Package Outline Dimensions



TO-252

Dimensions in inches and (millimeters)



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